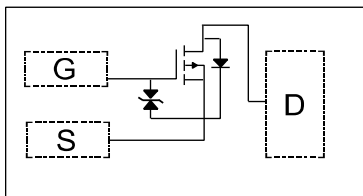


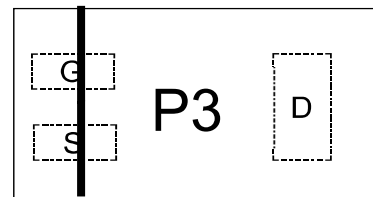
Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (mA)
-20	0.75@ V _{GS} =-4.5V	-300
	0.9@ V _{GS} =-2.5V	
	1.5@ V _{GS} =-1.8V	



Circuit Diagram



Marking (Top View)

Absolute maximum rating@25°C

Parameter	Symbol	Value	Units
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±10	V
Continuous Drain Current	Continuous	I _D	mA
	Pulsed	I _{DP}	
Source current(Body diode)	Continuous	I _S	mA
	Pulsed	I _{SP}	
Total power dissipation	P _D	150	mW
Channel temperature	T _J	150	°C
Range of storage temperature	T _{STG}	-55 to +150	°C

Thermal resistance

Parameter	Symbol	Limits	Units
Channel to ambient	R _{th(ch-a)}	833	°C/W

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D = -1mA, V_{GS} = 0V$	-20		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20V, V_{GS} = 0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$	-	-	± 2	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.5	-	-1.1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -300mA$	-	0.75	1.0	Ω
		$V_{GS} = -2.5V, I_D = -200mA$	-	0.9	1.5	Ω
		$V_{GS} = -1.8V, I_D = -100mA$		1.5	2.2	Ω
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -200mA$	0.3			s
Input Capacitance	C_{ISS}	$V_{GS} = 0V, V_{DS} = -10V,$ $f = 1MHz$	-	110		pF
Output Capacitance	C_{OSS}		-	9		pF
Reverse Transfer Capacitance	C_{RSS}		-	5		pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10V, V_{GS} = -4.5V,$ $R_G = 10\Omega, R_L = 100\Omega$ $I_D = -100mA$	-	5		ns
Turn-Off Delay Time	$t_{d(off)}$		-	15		ns
Turn-On Rise Time	t_r		-	4		ns
Turn-On Fall Time	t_f		-	13		ns
Total Gate Charge	Q_g	$V_{DD} = -10V, V_{GS} = -4.5V,$ $I_D = -200mA$ $R_G = 10\Omega, R_L = 50\Omega$		1.4		nC
Gate-Source Charge	Q_{gs}			0.3		nC
Gate-Drain Charge	Q_{gd}			0.3		nC
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = -200mA$		-	-1.2	V

Typical Characteristics

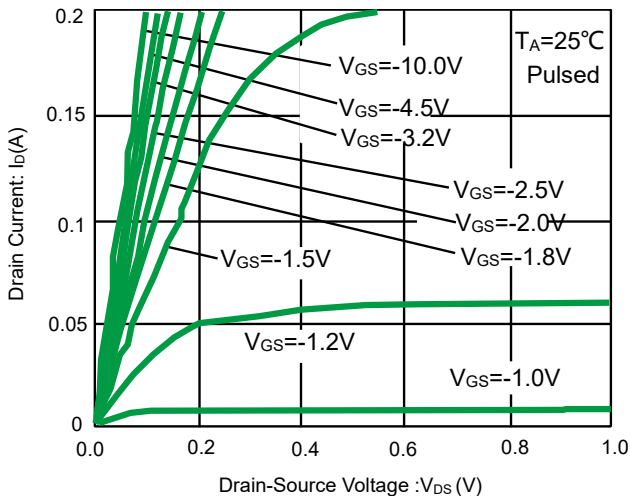


Fig 1. Typical output characteristics(I)

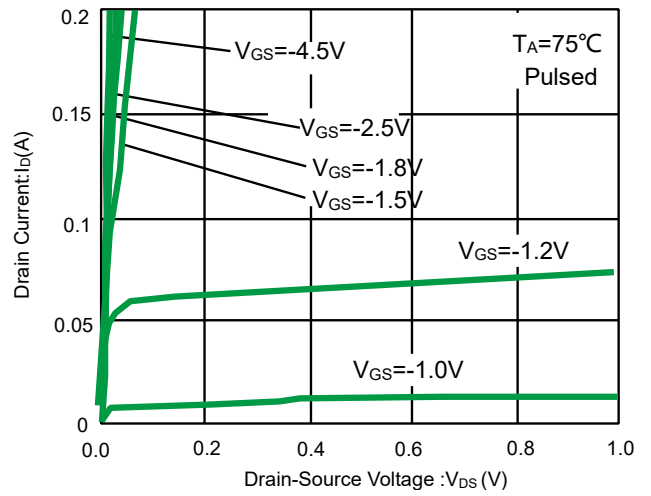


Fig 2. Typical output characteristics(II)

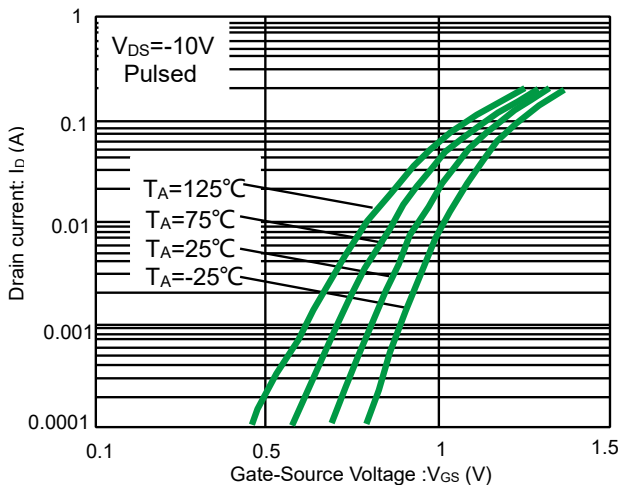


Fig 3. Typical transfer characteristics

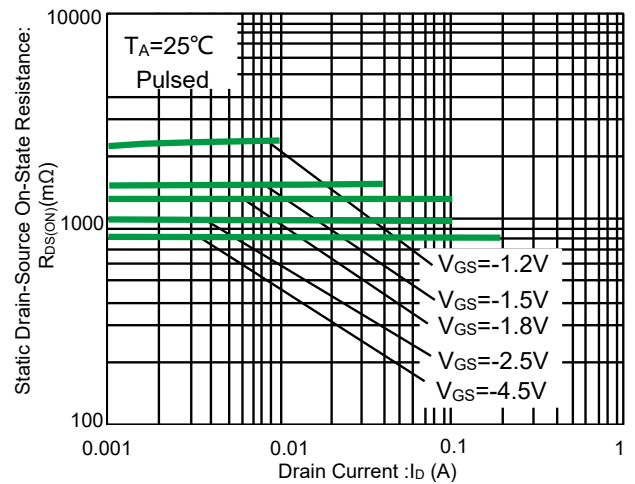


Fig 4. Static drain-source on-state resistance vs. drain current(I)

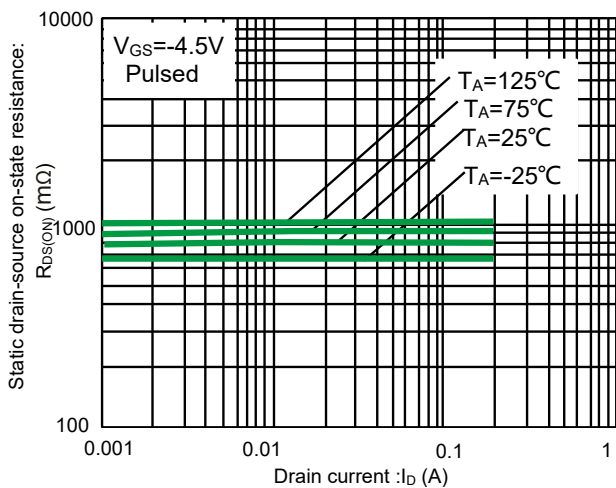


Fig 5. Static drain-source on-state resistance vs. drain current (II)

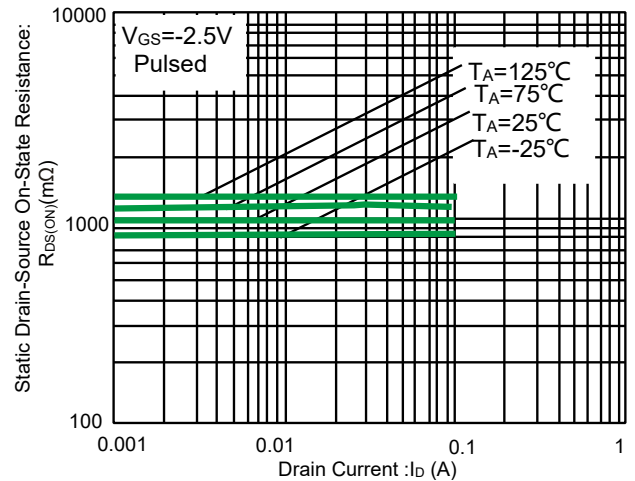


Fig 6. Static drain-source on-state resistance vs. drain current(III)

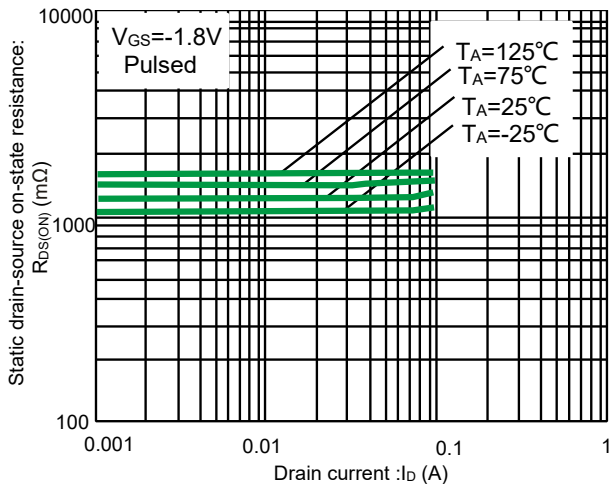


Fig 7. Static drain-source on-state resistance vs. drain current(I_D)

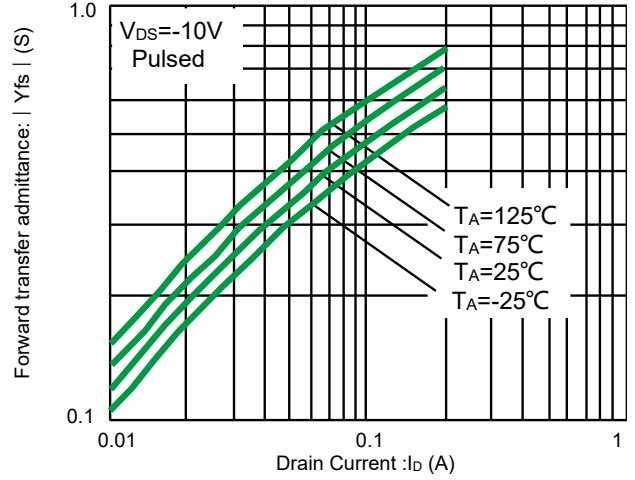


Fig 8. Forward transfer admittance vs. drain current

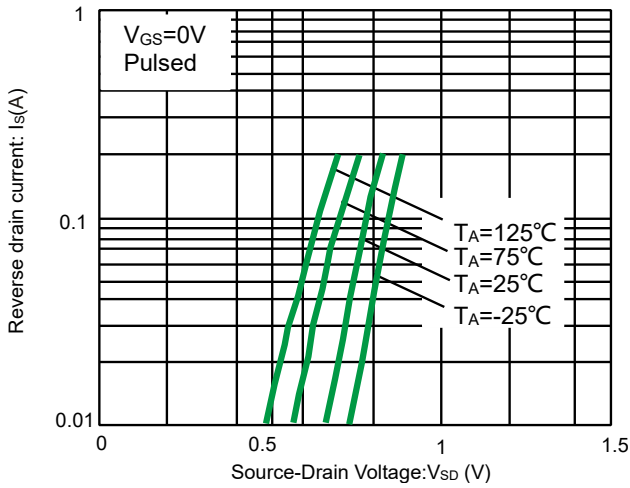


Fig 9. Reverse drain current vs. source-drain voltage

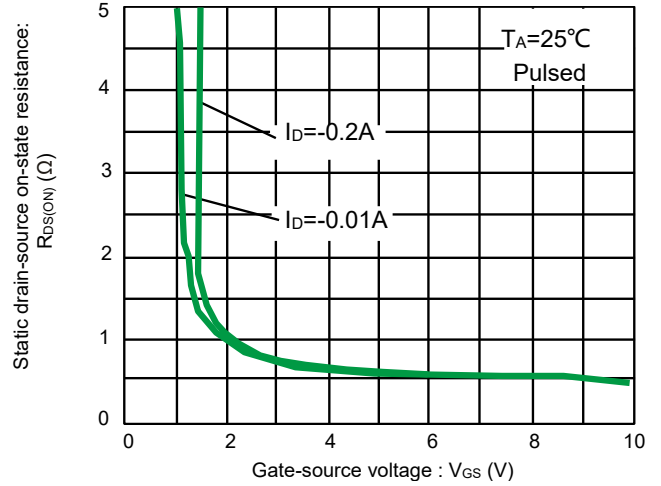


Fig 10. Static drain-source on-state resistance vs. gate source voltage

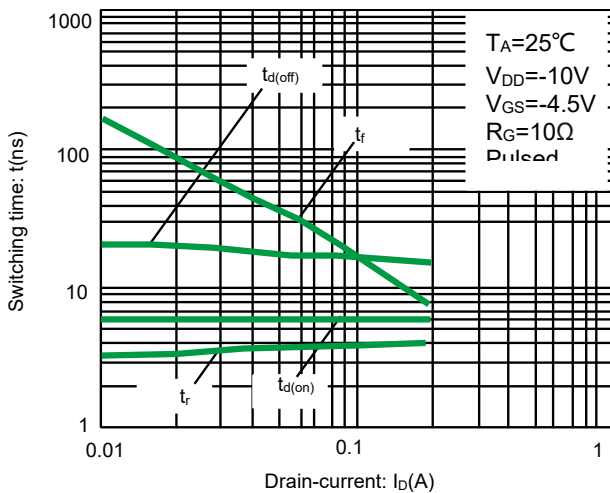


Fig 11. Switching characteristics

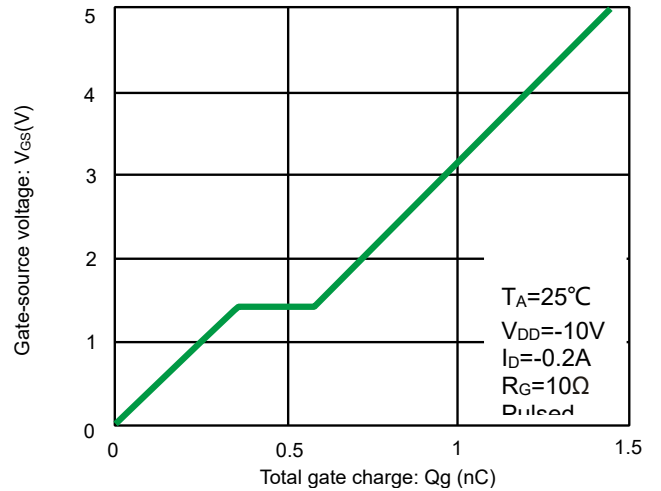


Fig 12. Dynamic input characteristics

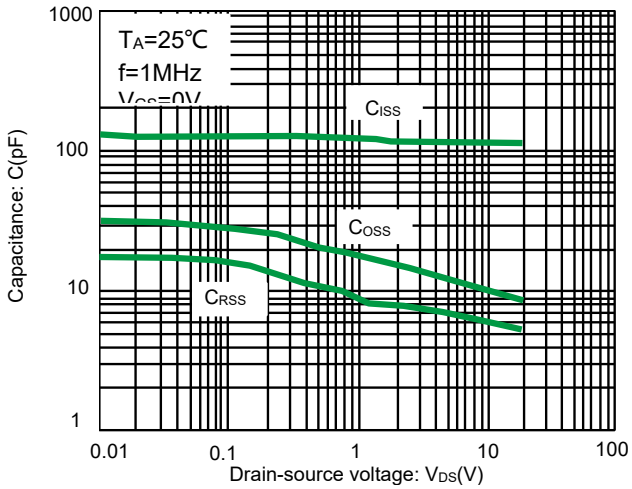


Fig 13. Typical capacitance vs. drain-source voltage

Measurement circuit

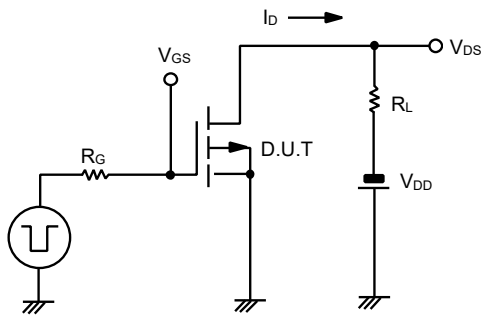


Fig.1-1 Switching time measurement circuit

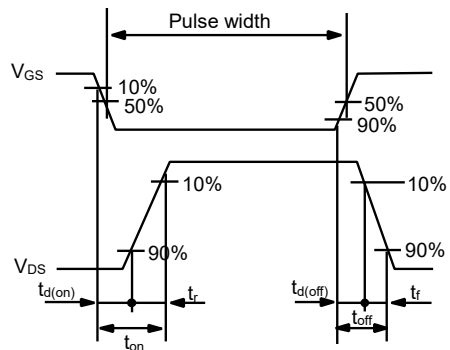


Fig.1-2 Switching time waveforms

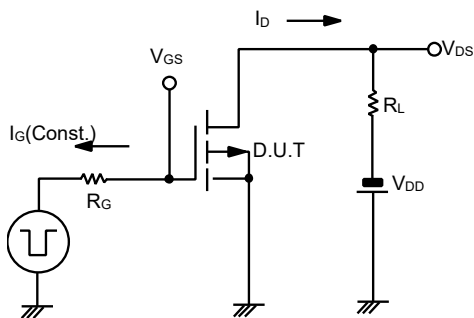


Fig.2-1 Gate charge measurement circuit

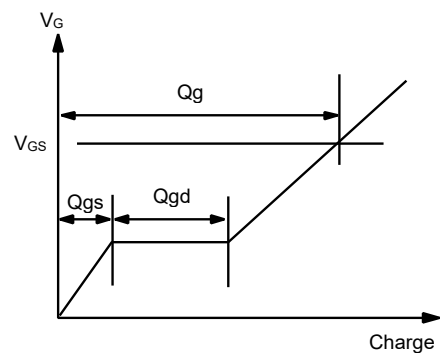
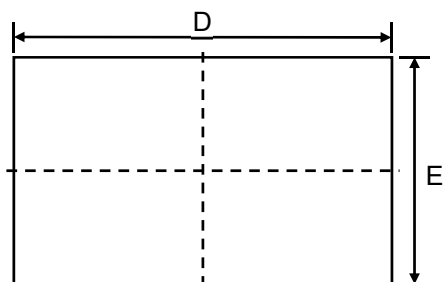
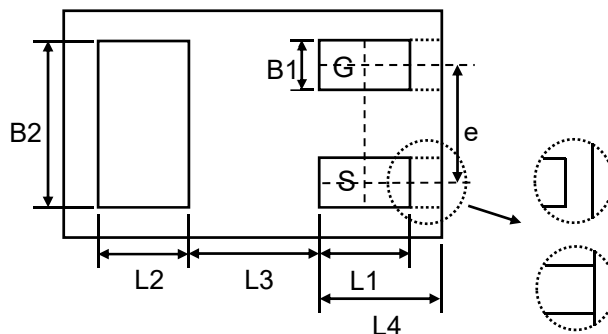


Fig.2-2 Gate charge waveform

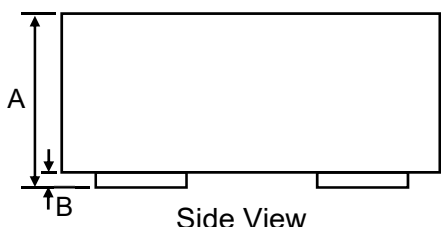
Product dimension (DFN1006-3L)



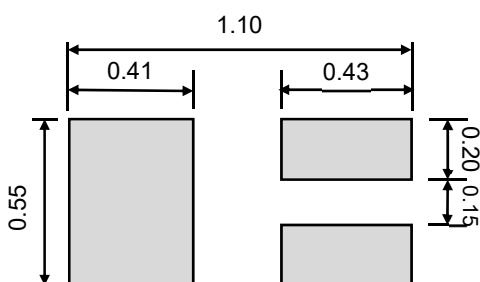
Top View



Bottom View



Side View

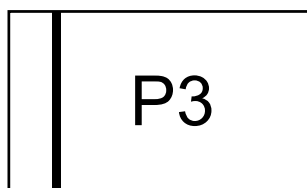


Suggested PCB Layout

Unit: mm

Dim	Millimeters		Inches	
	Min	Max	Min	Max
A	0.33	0.498	0.013	0.020
B	0.00	0.05	0.000	0.002
B1	0.10	0.20	0.004	0.008
B2	0.45	0.55	0.018	0.022
D	0.90	1.05	0.035	0.041
E	0.50	0.65	0.020	0.026
e	0.35		0.014	
L1	0.20	0.30	0.008	0.012
L2	0.20	0.30	0.008	0.012
L3	0.39		0.015	
L4	0.25	0.35	0.010	0.014

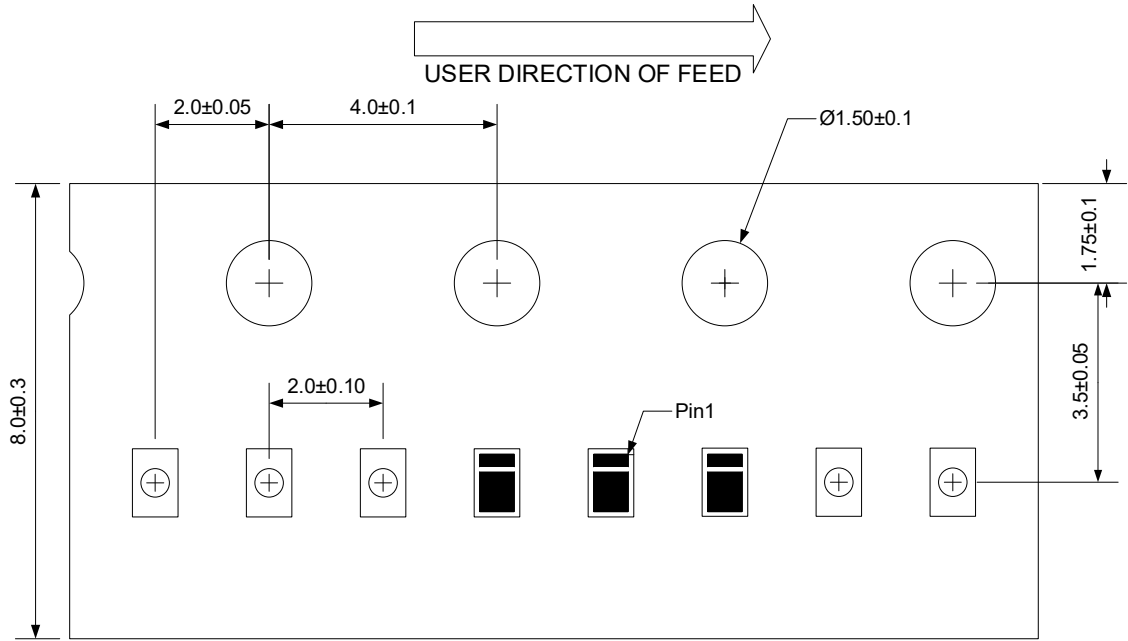
Marking information



Ordering information


Device	Package	Reel	Shipping
PPM3FD201E0	DFN1006-3L(Pb-Free)	7"	10000 / Tape & Reel

Load with information



Unit:mm


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